NL17SV08XV5T2

Single 2-Input AND Gate

The NL17SV08 is an ultra−high performance 2−Input AND gate manufactured in 0.35μ CMOS technology with excellent performance down to 0.9 volts. This device is ideal for extremely high−speed and high−drive applications. Additionally, limitations of board space are no longer a constraint. The very small SOT−553 makes this device fit most tight designs and spaces.

Features

- Extremely High Speed: t_{PD} = 1.0 ns (Typ) @ V_{CC} = 3.3 V
- Designed for 0.9 to 3.3 V Operation
- Overvoltage Tolerance (OVT)* Input Pins Permit Logic Translation
- Balanced ±24 mA Output Drive @ 3.3 V
- Near Zero Static Supply Current
- Ultra−Tiny SOT−553 5 Pin Package Only 1.6 x 1.6 x 0.6 mm
- All Devices in Package SOT−553 are Inherently Pb−Free

Typical Applications

- Cellular
- Digital Camera
- PDA
- Digital Video

Industry Standard

- Functionally Similar to NC7SV08 and SN74AUC1G08

*Overvoltage Tolerance (OVT) enables input pins to function outside (higher) of their operating voltages, with no damage to the devices or to signal integrity.

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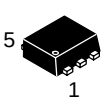
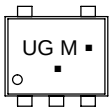
MARKING DIAGRAM

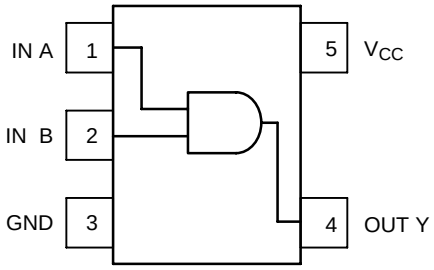


SOT−553
CASE 463B



UG = Specific Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

PIN DIAGRAM



PIN ASSIGNMENT

PIN #	FUNCTION
1	IN A
2	IN B
3	GND
4	OUT Y
5	V_{CC}

FUNCTION TABLE

Input A	Input B	Output Y
L	L	L
L	H	L
H	L	L
H	H	H

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Rating		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to + 4.6	V
V_I	DC Input Voltage		−0.5 to + 4.6	V
V_O	DC Output Voltage		−0.5 to V_{CC} +0.5	V
I_{IK}	DC Input Diode Current	V_I < GND	±50	mA
I_{OK}	DC Output Diode Current	V_O = GND V_O = V_{CC}	−50 +50	mA
I_O	DC Output Sink Current		±50	mA
I_{CC}	DC Supply Current per Supply Pin		±50	mA
I_{GND}	DC Ground Current per Ground Pin		±50	mA
T_{STG}	Storage Temperature Range		− 65 to +150	°C
T_L	Lead Temperature, 1.0 mm from Case for 10 seconds		260	°C
T_J	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 1)		250	°C/W
P_D	Power Dissipation in Still Air at 85°C		250	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 2 ounce copper trace no air flow.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		0.9	3.6	V
V_{IN}	Digital Input Voltage		0	3.6	V
V_{out}	Output Voltage		0	V_{CC}	V
I_{OH}/I_{OL}	Output Current	V_{CC} = 3.0 V to 3.6 V V_{CC} = 2.3 V to 2.7 V V_{CC} = 1.65 V to 1.95 V V_{CC} = 1.4 V to 1.6 V V_{CC} = 1.1 V to 1.3 V V_{CC} = 0.9 V		±24 ±18 ±6 ±4 ±2 ±0.1	mA
t_A	Operating Temperature Range. All Package Types		−40	+85	°C
t_r, t_f	Input Rise or Fall Time	V_{CC} = 3.3V ± 0.3 V	0	10	nS/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

DC CHARACTERISTICS– Digital Section (Voltages Referenced to GND)

Symbol	Parameter	Condition	V_{CC}	T_A = 25°C		T_A = −40 to 85°C		Unit
				Min	Max	Min	Max	
V_{IH}	High Level Input Voltage		0.90 1.10 ≤= V_{CC} ≤ 1.30 1.40 ≤ V_{CC} ≤ 1.60 1.65 ≤ V_{CC} ≤ 1.95 2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60	0.65 x V_{CC} 0.65 x V_{CC} 0.65 x V_{CC} 0.65 x V_{CC} 1.6 2.0		0.65 x V_{CC} 0.65 x V_{CC} 0.65 x V_{CC} 0.65 x V_{CC} 1.6 2.0		V
V_{IL}	Low Level Input Voltage		0.90 1.10 ≤ V_{CC} ≤ 1.30 1.40 ≤ V_{CC} ≤ 1.60 1.65 ≤ V_{CC} ≤ 1.95 2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60		0.35 x V_{CC} 0.35 x V_{CC} 0.35 x V_{CC} 0.35 x V_{CC} 0.7 0.8		0.35 x V_{CC} 0.35 x V_{CC} 0.35 x V_{CC} 0.35 x V_{CC} 0.7 0.8	V
V_{OH}	High Level Output Voltage	I_{OH} = −100 μA	0.90 1.10 ≤ V_{CC} ≤ 1.30 1.40 ≤ V_{CC} ≤ 1.60 1.65 ≤ V_{CC} ≤ 1.95 2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60	V_{CC} − 0.1 V_{CC} − 0.1 V_{CC} − 0.2 V_{CC} − 0.2 V_{CC} − 0.2 V_{CC} − 0.2		V_{CC} − 0.1 V_{CC} − 0.1 V_{CC} − 0.2 V_{CC} − 0.2 V_{CC} − 0.2 V_{CC} − 0.2		V
		I_{OH} = −2.0 mA	1.10 ≤ V_{CC} ≤ 1.30	0.75 x V_{CC}		0.75 x V_{CC}		
		I_{OH} = −4.0 mA	1.40 ≤ V_{CC} ≤ 1.60	0.75 x V_{CC}		0.75 x V_{CC}		
		I_{OH} = −6.0 mA	1.65 ≤ V_{CC} ≤ 1.95 2.30 ≤ V_{CC} ≤ 2.70	1.25 2.0		1.25 2.0		
		I_{OH} = −12 mA	2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60	1.8 2.2		1.8 2.2		
		I_{OH} = −18 mA	2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60	1.7 2.4		1.7 2.4		
		I_{OH} = −24 mA	2.70 ≤ V_{CC} ≤ 3.60	2.2		2.2		
V_{OL}	Low Level Output Voltage	I_{OL} = 100 μA	0.90 1.10 ≤ V_{CC} ≤ 1.30 1.40 ≤ V_{CC} ≤ 1.60 1.65 ≤ V_{CC} ≤ 1.95 2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60		0.1 0.1 0.2 0.2 0.2 0.2		0.1 0.1 0.2 0.2 0.2 0.2	V
		I_{OL} = 2.0 mA	1.10 ≤ V_{CC} ≤ 1.30		0.25 x V_{CC}		0.25 x V_{CC}	
		I_{OL} = 4.0 mA	1.40 ≤ V_{CC} ≤ 1.60		0.25 x V_{CC}		0.25 x V_{CC}	
		I_{OL} = 6.0 mA	1.65 ≤ V_{CC} ≤ 1.95		0.3		0.3	
		I_{OL} = 12 mA	2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60		0.4 0.4		0.4 0.4	
		I_{OL} = 18 mA	2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60		0.6 0.4		0.6 0.4	
		I_{OL} = 24 mA	2.70 ≤ V_{CC} ≤ 3.60		0.55		0.55	
I_{IN}	Input Leakage Current	0 = V_I = 3.6 V	0.90 to 3.60		±0.1		±0.9	μA
I_{OFF}	Power Off Leakage Current		0		10		10	μA
I_{CC}	Quiescent Supply Current	V_I = V_{CC} or GND	0.90 to 3.60		0.9		5	μA

AC CHARACTERISTICS (Input $t_r = t_f = 3.0$ nS)

Symbol	Parameter	−40°C		25°C			85°C		Unit
		Condition	V_{CC}	Min	Typ	Max	Min	Max	
T_{PHL}, T_{PLH}	Propagation Delay	C_L = 15 pF, R_L = 1.0 MΩ	0.90		13				nS
		C_L = 15 pF, R_L = 2.0 kΩ	1.10 ≤ V_{CC} ≤ 1.30 1.40 ≤ V_{CC} ≤ 1.60	3.0 1.0	6.0 3.2	10.0 6.0	1.0 1.0	14.6 7.2	nS
		C_L = 30 pF, R_L = 500 kΩ	1.65 ≤ V_{CC} ≤ 1.95 2.30 ≤ V_{CC} ≤ 2.70 2.70 ≤ V_{CC} ≤ 3.60	1.0 0.8 0.7	2.0 1.2 1.0	4.5 2.6 2.3	1.0 0.7 0.6	5.3 3.7 3.0	nS
C_{IN}	Input Capacitance		0		2.0				pF
C_{OUT}	Output Capacitance		0		4.5				pF
C_{PD}	Power Dissipation Capacitance	V_I = 0 V or V_{CC} F = 10 MHz	0.90 to 3.60		20				pF

ORDERING INFORMATION

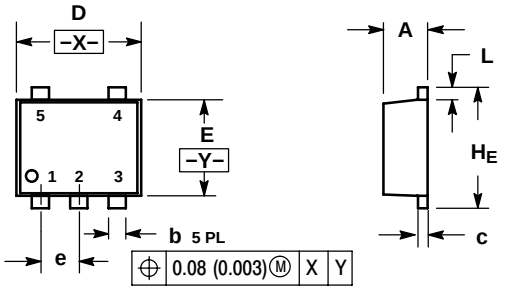
Device Order Number	Package Type	Shipping†
NL17SV08XV5T2	SOT−553*	178 mm, 4000 Units / Tape & Reel
NL17SV08XV5T2G	SOT−553*	178 mm, 4000 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb−Free.

NL17SV08XV5T2

PACKAGE DIMENSIONS

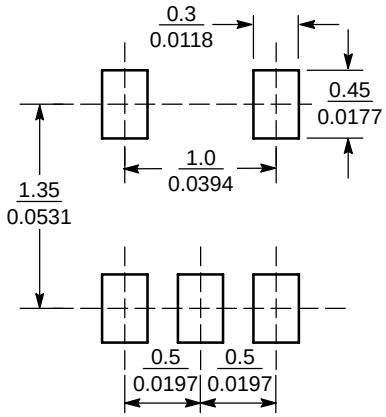
SOT−553
5−LEAD PACKAGE
CASE 463B−01
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.022	0.024
b	0.17	0.22	0.27	0.007	0.009	0.011
c	0.08	0.13	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.063	0.067
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.50 BSC			0.020 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H_E	1.50	1.60	1.70	0.059	0.063	0.067

SOLDERING FOOTPRINT*



SCALE 20:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
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Phone: 81−3−5773−3850

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